Amendment to the Claims:

This listing of claims replaces all prior versions and listings of claims in the application:

1.(Currently Amended)   A gap fill test pattern for a shallow trench isolation (STI) gap fill, .
comprising:

    a.   a test region ~~comprising an outer circumference~~ defining a first interior area <u>and a</u>

<u>second interior area</u>; and

    b.   a test pattern disposed <u>with</u>in the first interior area, the test pattern fabricated

using a shallow trench adapted for testing of shallow trench isolation gap fill, the test

pattern ~~defining~~ <u>comprising</u> a border ~~to a~~ <u>at least partially enclosing the</u> second interior

area.

2.(Currently Amended)   The gap fill test pattern of claim 1, wherein the test region ~~is at least~~

<u>comprises</u> one of (i) a square rectangular region, (ii) a non-square rectangular region, ~~or~~ <u>and</u> (iii)

a substantially orthogonal region ~~defining a border comprising at least one discontinuity~~.

3.(Original) The gap fill test pattern of claim 2, wherein:

    a.   the square rectangular region comprises an area of around 1 μm^2;

    b.   the test pattern border defines a square comprising an area of around 0.09

μm^2;and

    c.   a width of the test pattern border is from around 0.085 μm to around 0.200 μm.

4.(Currently Amended) The gap fill test pattern of claim 2, wherein:

a.   the non-square rectangular region comprises an area of around from around 1 μm^2 to around 3 μm^2;

b.   the test pattern defines a rectangle, ~~comprising border~~ comprising a width of around 0.3 μm, the test pattern rectangle further comprising a height of around one-half the height of the rectangular region and a width of from around 0.085 μm to around 0.200 μm.

5.(Currently Amended) The gap fill test pattern of claim 1, wherein the test pattern <u>border</u> comprises ~~at least~~ one of (i) a <u>continuous</u> rectangle ~~with a contiguous border or~~ <u>and</u> (ii) a <u>discontinuous</u> rectangle ~~with~~ formed by at least one discontinuity ~~in its border~~.

6.(Currently Amended) The gap fill test pattern of claim 5, wherein the <u>continuous</u> rectangle ~~with a contiguous border~~ is adapted to simulate a corner region of a static random access memory cell.

7.(Currently Amended) The gap fill test pattern of claim 5, wherein the <u>discontinuous</u> rectangle ~~with at least one discontinuity in its border~~ is adapted to simulate an outer diameter line end region of a static random access memory cell.

8.(Currently Amended) The gap fill test pattern of claim 5, wherein the ~~rectangle with~~ at least one discontinuity ~~in its border comprises a discontinuity~~ <u>forms a gap</u> of around 0.1 μm.

9.(Currently Amended) The gap fill test pattern of claim 5, wherein the <u>discontinuous</u> rectangle ~~with at least one discontinuity in its border~~ comprises two discontinuous border segments, each comprising a first section intersecting a second section at a substantially right angle.

10.(Currently Amended) A gap fill test region pattern for a shallow trench isolation (STI) gap fill, comprising:

    a.   test area fabricated on a predetermined region of a semiconductor wafer, the test area further comprising a border and a ~~first interior~~ <u>test region</u> area;

    b.   a plurality of test regions disposed within the ~~first interior~~ <u>test region</u> area, each test region further comprising:

        i.   an outer circumference;

        ii.   ~~an~~ <u>a first</u> interior area; and

        iii.   a ~~rectangular~~ test pattern disposed in the <u>first</u> interior area, the test pattern ~~defining~~ <u>comprising</u> a border ~~to~~ <u>at least partially enclosing</u> a ~~third~~ <u>second</u> interior area, the test pattern further comprising at least one shallow trench adapted for testing of shallow trench isolation gap fill.

11.(Currently Amended) The gap fill test ~~layout~~ <u>region pattern</u> of claim 10, further comprising:

    a.   an array of first rectangular test regions disposed within the grid, each first rectangular test region occupying a unique grid cell defined by a column and row of the grid; and

    b.   an array of second rectangular test regions disposed within the grid, each second rectangular test region occupying a unique grid cell defined by a column and row of the

grid, the second rectangular test regions further comprising at least one dimension which differs from the dimensions of the first rectangular test regions.

12.(Currently Amended) The gap fill test ~~layout~~ region pattern of claim 11, wherein:

    a.   the first rectangular test regions are squares.

13.(Currently Amended) The gap fill test ~~layout~~ region pattern of claim 12, further comprising:

    a.   an array of third rectangular test regions disposed within the grid, each third rectangular test region occupying a unique grid cell defined by a column and row of the grid, the third rectangular test regions further comprising at least one dimension which differs from a dimension of the first rectangular test regions and at least one dimension which differs from a dimension of the second rectangular test regions.